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32. (New) The semiconductor device according to claim 31, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

33. (New) The semiconductor device according to claim 32, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

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REMARKS

After the foregoing amendment, claims 25-33 will be pending in the present application. Claims 1-15 have been canceled without intending to abandon or publicly dedicate any patentable subject matter and claims 25-33 are new. No new matter has been added by the amendment. Reconsideration and allowance of the application, as amended, are respectfully requested.

The present invention is directed to a semiconductor device that includes a passivation film located to cover the surface of a semiconductor substrate and wirings. The passivation film includes a first insulating film that contains at least one impurity selected from the group consisting of argon, boron, nitrogen and phosphorus, which improves the insulation resistive properties of the first insulating film. In particular, the moisture resistive properties of the insulating film are improved.

Okumura et al. discloses a semiconductor device having an SOG layer 13 as an interlayer insulation film. An impurity is ion-implanted into the SOG layer 13. However, Okumura et al. does not teach or suggest a passivation film that covers the surface of a semiconductor substrate. Okumura et al. discloses wirings comprising a polysilicon layer 16 and a silicide layer 17, which

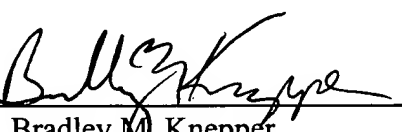
do not act as an insulation layer that insulates and protects wirings by covering the surface of the semiconductor substrate. That is, Okumura et al. does not provide a motivation to provide a passivation film covering the surface of the semiconductor substrate to improve insulation resistive properties.

In view of the foregoing remarks, it is respectfully submitted that the present application, including claims 25-33, is in condition for allowance and such action is respectfully requested. The Examiner is invited to contact the undersigned by telephone if doing so would expedite the resolution of this case.

Respectfully submitted,

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